AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A flip-chip-type gallium nitride compound semiconductor light-emitting device comprising a substrate, an n-type semiconductor layer, a light-emitting layer, and a p-type semiconductor layer,

wherein a negative electrode is provided on said n-type semiconductor layer, and a positive electrode is provided on said p-type semiconductor layer;

the n-type semiconductor layer, the light-emitting layer, and the p-type semiconductor layer being successively provided atop said substrate in this order and being composed of a gallium nitride compound semiconductor,

wherein said positive electrode has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is in contact with said p-type semiconductor layer, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 1000 Å to 3,000 Å, and a bonding pad layer provided on said adhesion layer and being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals;

wherein the bonding pad layer is provided atop a portion less than the entirety of the ohmic electrode layer, and that the adhesion layer has the same dimension as the bonding pad layer.

2. (canceled).

3. (canceled).

4. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said ohmic electrode layer has a thickness of 100 Å to 3,000 Å.

5. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 4, wherein said ohmic electrode layer has a thickness of 500 Å to 2,000 Å.

6. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said bonding pad layer has a thickness of at least 1,000 Å.

7. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 6, wherein said bonding pad layer has a thickness of 3,000 Å to 5,000 Å.

8. (previously presented): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said bonding pad layer is composed of gold.

9. (currently amended): A positive electrode for use in a gallium nitride compound semiconductor light-emitting device, wherein said positive electrode has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is brought into contact with a p-type semiconductor layer of said gallium nitride compound semiconductor light-emitting device, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 1000 Å to 3,000 Å , and a bonding pad layer provided on said adhesion layer, said bonding pad layer being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals; wherein the bonding pad layer is provided atop a portion less than the entirety of the ohmic electrode layer, and that the adhesion layer has the same dimension as the bonding pad layer.

10. (canceled).

11. (canceled).

12. (previously presented): A light-emitting diode comprising a flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1.

13. (canceled).